

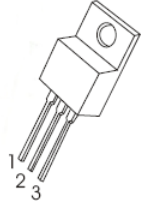


TO-220-3L Plastic-Encapsulate Transistors

MJE3055 TRANSISTOR (NPN)

TO-220-3L

1. BASE
2. COLLECTOR
3. EMITTER



FEATURES

- General Purpose and Switching Applications

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	70	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	10	A
P _C	Collector Power Dissipation	2	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =1mA, I _E =0	70			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =200mA, I _B =0	60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	5			V
Collector cut-off current	I _{CB0}	V _{CB} =70V, I _E =0			1	mA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			5	mA
DC current gain	h _{FE(1)} *	V _{CE} =4V, I _C =4A	20		100	
	h _{FE(2)} *	V _{CE} =4V, I _C =10A	5			
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =4A, I _B =0.4A			1.1	V
	V _{CE(sat)} *	I _C =10A, I _B =3.3A			8	V
Base-emitter voltage	V _{BE} *	V _{CE} =4V, I _C =4A			1.8	V
Transition frequency	f _T	V _{CE} =10V, I _C =0.5A	2			MHz

Note:*Pulse test: t_p≤300μS, δ≤0.02.

Typical Characteristics

MJE3055

